

Vishay Semiconductors

## Thyristor High Voltage, Phase Control SCR, 16 A



PRIMARY CHARACTERISTICS							
I <sub>T(AV)</sub> 10 A							
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V, 1200 V						
$V_{TM}$	1.4 V						
I <sub>GT</sub>	60 mA						
T <sub>J</sub>	-40 °C to 125 °C						
Package	TO-220AB 3L						
Circuit configuration	Single SCR						

#### **FEATURES**

- Designed and qualified according to JEDEC®-JESD 47
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



#### **APPLICATIONS**

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

### **DESCRIPTION**

The VS-16TTS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operating up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS						
Capacitive input filter T <sub>A</sub> = 55 °C, T <sub>J</sub> = 125 °C, common heatsink of 1 °C/W	13.5	17	А						

MAJOR RATINGS	MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS							
I <sub>T(AV)</sub>	Sinusoidal waveform	10	A							
I <sub>RMS</sub>		16	A							
V <sub>DRM</sub> /V <sub>RRM</sub>	Range (1)	800, 1200	V							
I <sub>TSM</sub>		200	А							
V <sub>T</sub>	10 A, T <sub>J</sub> = 25 °C	1.4	V							
dV/dt		500	V/µs							
dl/dt		150	A/µs							
T <sub>J</sub>	Range	-40 to +125	°C							

#### Note

(1) For higher voltage up to 1600 V contact factory

VOLTAGE RATINGS									
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA						
VS-16TTS08-M3	800	800	10						
VS-16TTS12-M3	1200	1200	10						

# VS-16TTS08-M3, VS-16TTS12-M3

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ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL		TEST CONDITIONS	VAL	UNITS			
PARAMETER	TEST CONDITIONS		TEST CONDITIONS	TYP.	MAX.	ONTO		
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 98 °C, 1	80° conduction, half sine wave	1				
Maximum RMS on-state current	I <sub>RMS</sub>			1	6	Α		
Maximum peak, one-cycle,	L	10 ms sine p	ulse, rated V <sub>RRM</sub> applied	1	70			
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine p	10 ms sine pulse, no voltage reapplied					
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine p	ulse, rated V <sub>RRM</sub> applied	144		A <sup>2</sup> s		
waximum i-t for fusing	1-1	10 ms sine pulse, no voltage reapplied			200			
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 to 10 r	t = 0.1 to 10 ms, no voltage reapplied			A²√s		
Maximum on-state voltage drop	$V_{TM}$	10 A, T <sub>J</sub> = 25	°C	1.4		V		
On-state slope resistance	r <sub>t</sub>	T <sub>.1</sub> = 125 °C		24.0		mΩ		
Threshold voltage	V <sub>T(TO)</sub>	1j=125 C		1.1		V		
Maximum reverse and direct leakage current	1 /1	T <sub>J</sub> = 25 °C	V - Botod V A	0	.5			
waximum reverse and direct leakage current	$I_{RM}/I_{DM}$	T <sub>J</sub> = 125 °C	$V_R = Rated V_{RRM}/V_{DRM}$	1	0			
Holding current	l <sub>Η</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A 16TTS08PbF, 16TTS12PbF, $T_J$ = 25 °C		-	150	mA		
Maximum latching current	IL	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C			00			
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 ^{\circ}\text{C}, V_{DRM} = R_g - k = \text{Open}$			00	V/µs		
Maximum rate of rise of turned-on current	dI/dt			150		A/µs		

TRIGGERING	TRIGGERING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Maximum peak gate power	P <sub>GM</sub>		8.0	W					
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV					
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α					
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V					
	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C	90	mA					
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	60						
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	35						
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C	3.0						
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0	v					
voltage to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	V					
Maximum DC gate voltage not to trigger	$V_{GD}$	T <sub>.I</sub> = 125 °C, V <sub>DRM</sub> = Rated value	0.25						
Maximum DC gate current not to trigger	$I_{GD}$	ij = 125 G, v <sub>DRM</sub> = nated value	2.0	mA					

SWITCHING								
PARAMETER SYMBOL TEST CONDITIONS VALUES U								
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9					
Typical reverse recovery time	t <sub>rr</sub>	T. – 125 °C	4	μs				
Typical turn-off time	tq	T <sub>J</sub> = 125 °C	110					

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THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C			
Maximum thermal resistance, junction to case		R <sub>thJC</sub>	DC operation	1.3				
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		62	°C/W			
Typical thermal resistance, case to heatsink	•		Mounting surface, smooth and greased	0.5				
Approximate weight				2	g			
Approximate weight				0.07	OZ.			
Mounting torque	minimum			6 (5)	kgf · cm			
Mounting torque -	maximum			12 (10)	(lbf · in)			
Marking daying			Consisted TO 220AB 21	16T	ΓS08			
Marking device			Case style TO-220AB 3L	16T7	ΓS12			

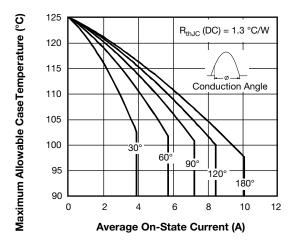


Fig. 1 - Current Rating Characteristics

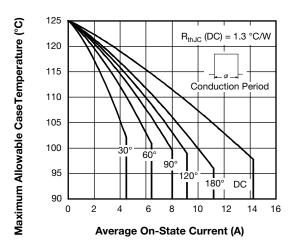


Fig. 2 - Current Rating Characteristics

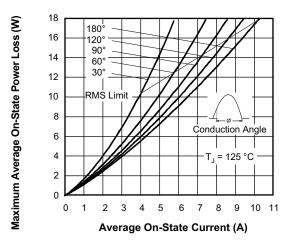


Fig. 3 - On-State Power Loss Characteristics

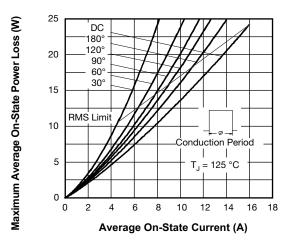


Fig. 4 - On-State Power Loss Characteristics



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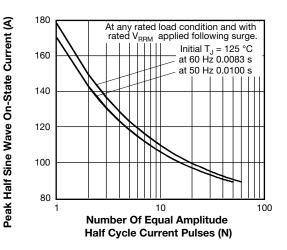


Fig. 5 - Maximum Non-Repetitive Surge Current

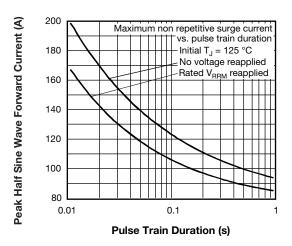


Fig. 6 - Maximum Non-Repetitive Surge Current

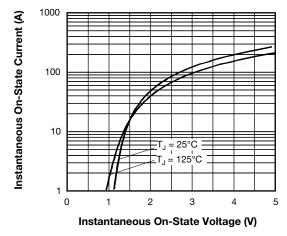


Fig. 7 - On-State Voltage Drop Characteristics

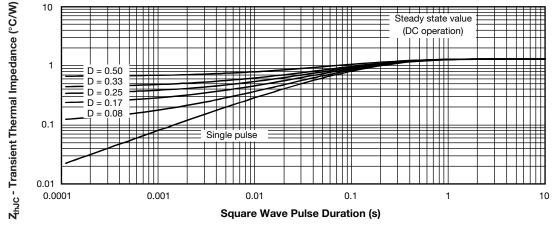


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

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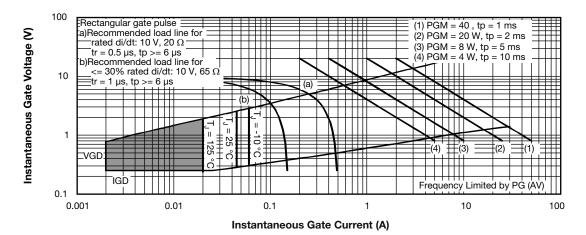


Fig. 9 - Gate Characteristics

### **ORDERING INFORMATION TABLE**

**Device code** VS-16 т Т S 12 -M3 2 3 5 4 6 Vishay Semiconductors product Current rating Circuit configuration: T = single thyristor Package: T = TO-220AB 5 Type of silicon: S = converter grade 08 = 800 VVoltage code x 100 = V<sub>RRM</sub> 12 = 1200 V Environmental digit:

ORDERING INFORMATION (Example)								
PREFERRED P/N BASE QUANTITY PACKAGING DESCRIPTION								
VS-16TTS08-M3	50	Antistatic plastic tubes						
VS-16TTS12-M3	50	Antistatic plastic tubes						

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

LINKS TO RELATED DOCUMENTS						
Dimensions <u>www.vishay.com/doc?96154</u>						
Part marking information	www.vishay.com/doc?95028					



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### **TO-220AB 3L**

#### **DIMENSIONS** in millimeters and inches





Conforms to JEDEC® outline TO-220AB

SYMBOL	MILLIM	IETERS	INC	HES	NOTES	NOTES		MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183			D2	11.68	13.30	0.460	0.524	6, 7
A1	1.14	1.40	0.045	0.055			Е	10.11	10.51	0.398	0.414	3, 6
A2	2.50	2.92	0.098	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			е	2.41	2.67	0.095	0.105	
b1	0.38	0.97	0.015	0.038	4		e1	4.88	5.28	0.192	0.208	
b2	1.20	1.73	0.047	0.068			H1	6.09	6.48	0.240	0.255	6
b3	1.14	1.73	0.045	0.068	4		L	13.52	14.02	0.532	0.552	
С	0.36	0.61	0.014	0.024			L1	3.32	3.82	0.131	0.150	2
c1	0.36	0.56	0.014	0.022	4		ØΡ	3.54	3.91	0.139	0.154	
D	14.85	15.35	0.585	0.604	3		Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355								

#### **Notes**

- <sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2



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